

TOSHIBA PHOTO TRANSISTOR SILICON NPN EPITAXIAL PLANAR

TPS612

FOR PHOTO SENSOR

Unit in mm

PHOTOELECTRIC COUNTER

FLOPPY DISK DRIVE

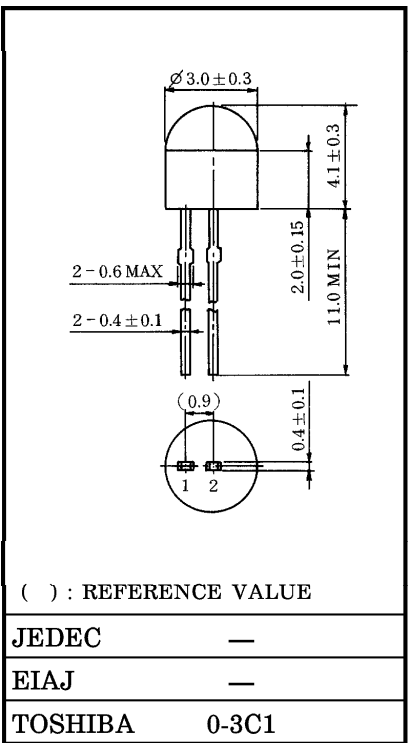
POSITION DETECTION

CONTROLLER OF HOME ELECTRIC EQUIPMENT

- $\phi 3\text{mm}$ resin package (black)
- About medium sensitivity
- Half value angle : $\theta_{\frac{1}{2}} = \pm 30^\circ$ (TYP.)
- The same size TLN113 is available as in infrared LED.
- Protected from external light by black mold packaging.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Collector Voltage	V_{ECO}	5	V
Collector Current	I_C	20	mA
Collector Power Dissipation	P_C	75	mW
Collector Power Dissipation Derating ($T_a > 25^\circ\text{C}$)	$\Delta P_C / ^\circ\text{C}$	-1	mW / $^\circ\text{C}$
Operating Temperature Range	T_{opr}	$-20 \sim 75$	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-30 \sim 100$	$^\circ\text{C}$

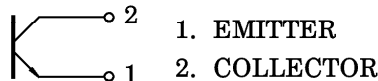


() : REFERENCE VALUE

JEDEC	—
EIAJ	—
TOSHIBA	0-3C1

Weight : 0.08g (TYP.)

PIN CONNECTION



961001EAA2

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OPTO-ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Dark Current		$I_D (I_{CEO})$	$V_{CE} = 10V, E = 0$	—	0.01	0.1	μA
Light Current		I_L (Note 1)	$V_{CE} = 3V, E = 0.1mW / cm^2$ (Note 2)	14	—	180	μA
Collector-Emitter Saturation Voltage		$V_{CE} (sat)$	$I_C = 7\mu A, E = 0.1mW / cm^2$ (Note 2)	—	0.2	0.4	V
Switching Time	Rise Time	t_r	$V_{CC} = 10V, I_C = 1mA$ $R_L = 100\Omega$	—	4	—	μs
	Fall Time	t_f		—	3	—	
Peak Sensitivity Wavelength		λ_P	—	—	870	—	nm
Half Value Angle		$\theta_{\frac{1}{2}}$	—	—	± 30	—	°

Note 1. I_L Classification AB : 14~60 μA , BC : 24~105 μA , A : 14~35 μA , B : 24~60 μA ,
C : 42~105 μA

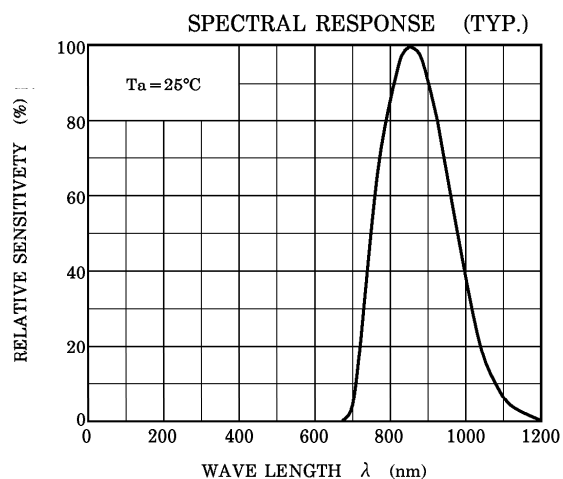
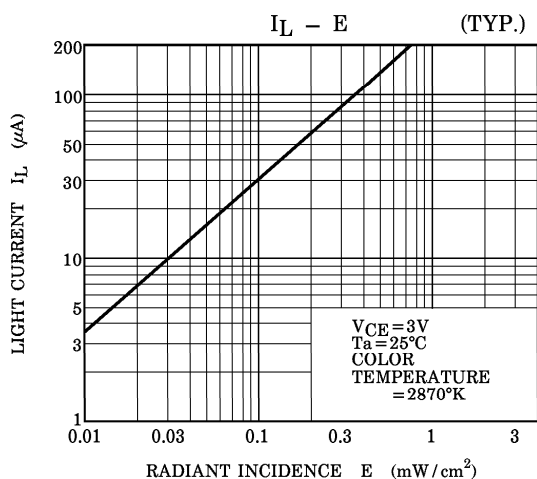
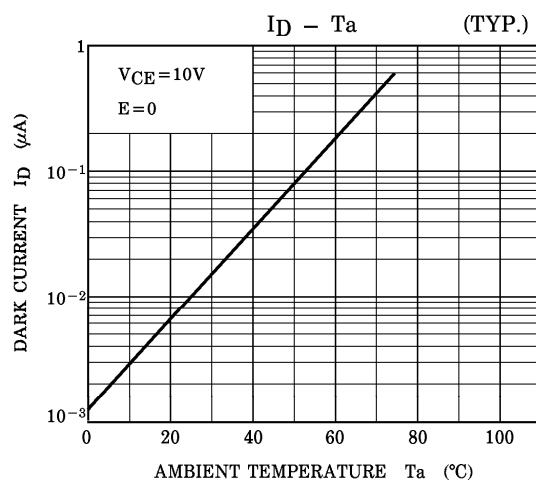
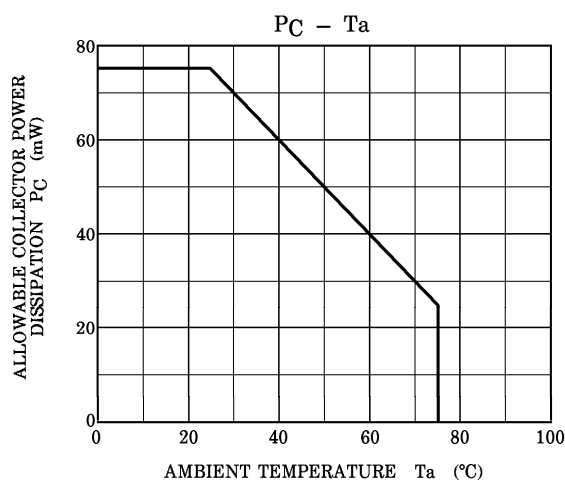
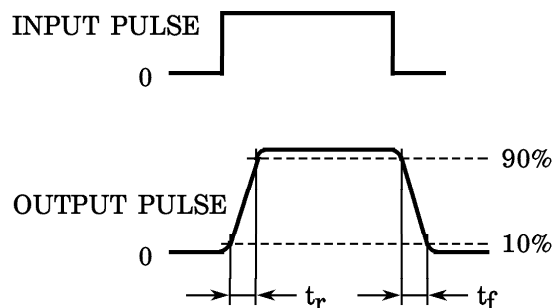
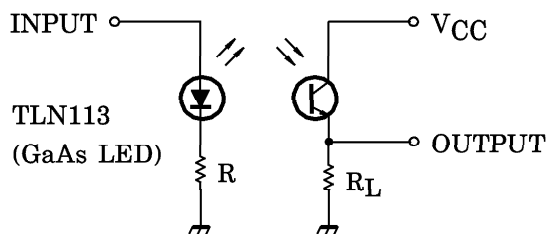
Note 2. Color temperature = 2870°K, Standard Tungsten Lamp.

PRECAUTION

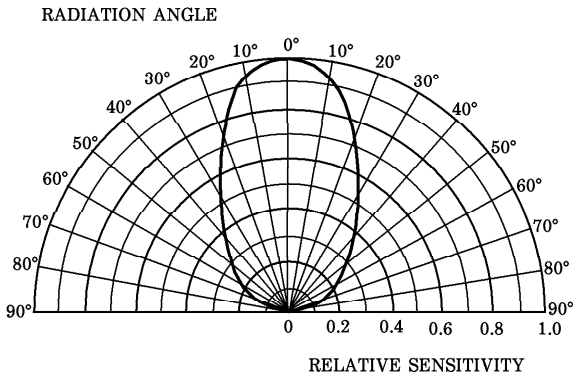
Please be careful of the followings.

1. Soldering temperature : 260°C MAX. Soldering time : 3s MAX.
(Soldering portion of lead : above 1.5mm from the body of the device)
2. If the lead is formed, the lead should be formed at a distance of 2mm from the body of the device.
Soldering shall be performed after lead forming.

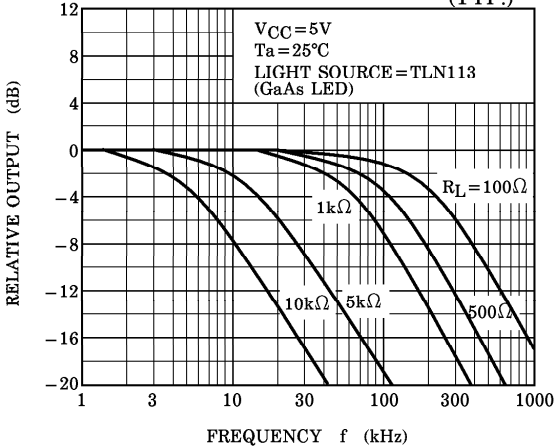
Fig. 1 SWITCHING TIME TEST CIRCUIT



DIRECTIONAL SENSITIVITY CHARACTERISTIC
(TYP.)
($T_a = 25^\circ\text{C}$)



FREQUENCY CHARACTERISTICS
(TYP.)



SWITCHING CHARACTERISTICS
(TYP.)

